

EH1525SJTS-1.8432M

EU RoHS
2011/65 +
2015/863
COMPLIANT

China RoHS

COMPLIANT

REACH
SVHC 163
Jun 15, 2015
COMPLIANT



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 3.3Vdc J-Lead 9.8mm x 14.0mm Plastic Surface Mount (SMD)
1.8432MHz ± 25 ppm 0°C to +70°C

ELECTRICAL SPECIFICATIONS

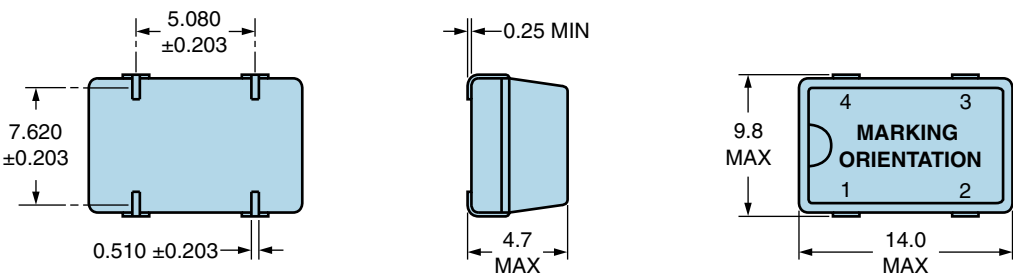
Nominal Frequency	1.8432MHz
Frequency Tolerance/Stability	± 25 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	± 5 ppm/year Maximum
Operating Temperature Range	0°C to +70°C
Supply Voltage	3.3Vdc $\pm 10\%$
Input Current	35mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.7Vdc Minimum, IOH = -8mA
Output Voltage Logic Low (Vol)	0.5Vdc Maximum, IOL = +8mA
Rise/Fall Time	6nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 $\pm 10\%$ (Measured at 50% of waveform)
Load Drive Capability	30pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	70% of Vdd Minimum to enable output, 20% of Vdd Maximum to disable output, No Connect to enable output.
Absolute Clock Jitter	± 250 pSec Maximum, ± 100 pSec Typical
One Sigma Clock Period Jitter	± 50 pSec Maximum, ± 40 pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A (Internal Crystal Only)
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C (Internal Crystal Only)
Mechanical Shock	MIL-STD-202, Method 213, Condition C
Moisture Resistance	MIL-STD-883, Method 1004
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

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MECHANICAL DIMENSIONS (all dimensions in millimeters)

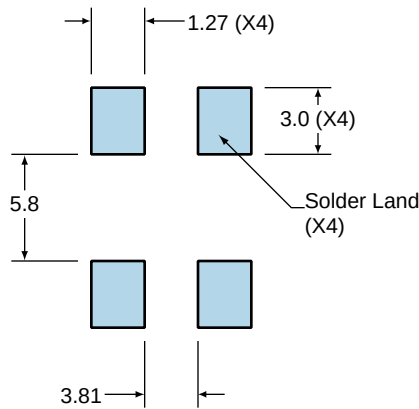


PIN	CONNECTION
1	Tri-State (High Impedance)
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	1.8432M
3	XXXXXX XXXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

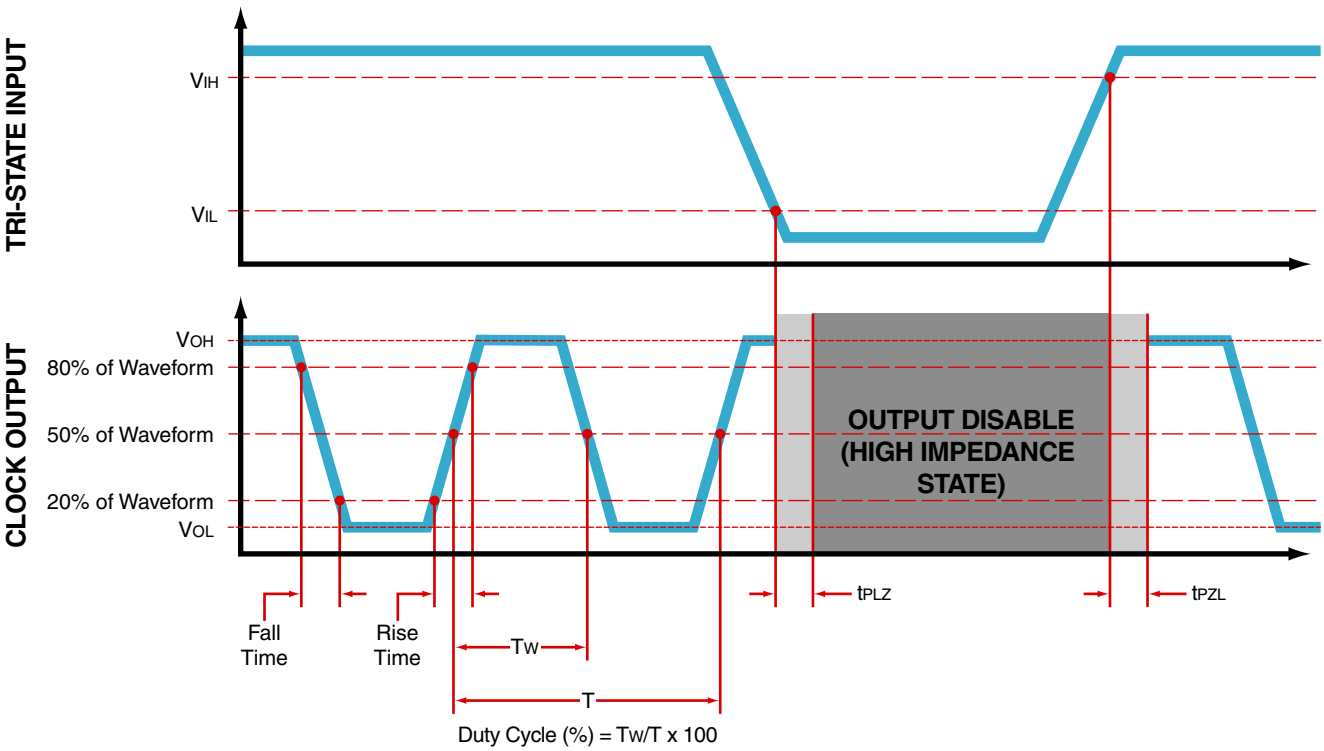
All Dimensions in Millimeters



All Tolerances are ±0.1

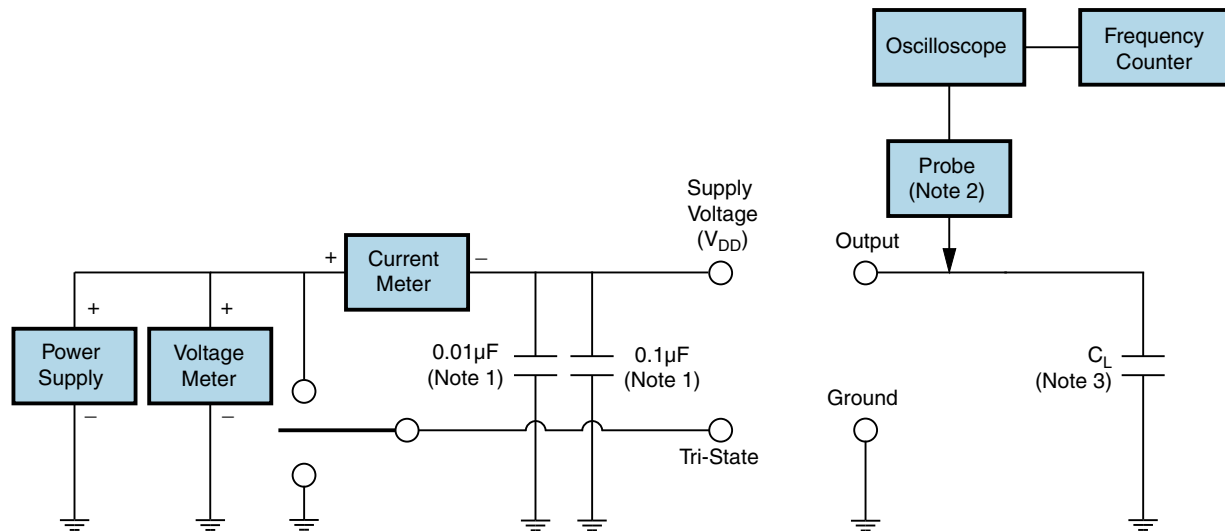
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OUTPUT WAVEFORM & TIMING DIAGRAM



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Test Circuit for CMOS Output



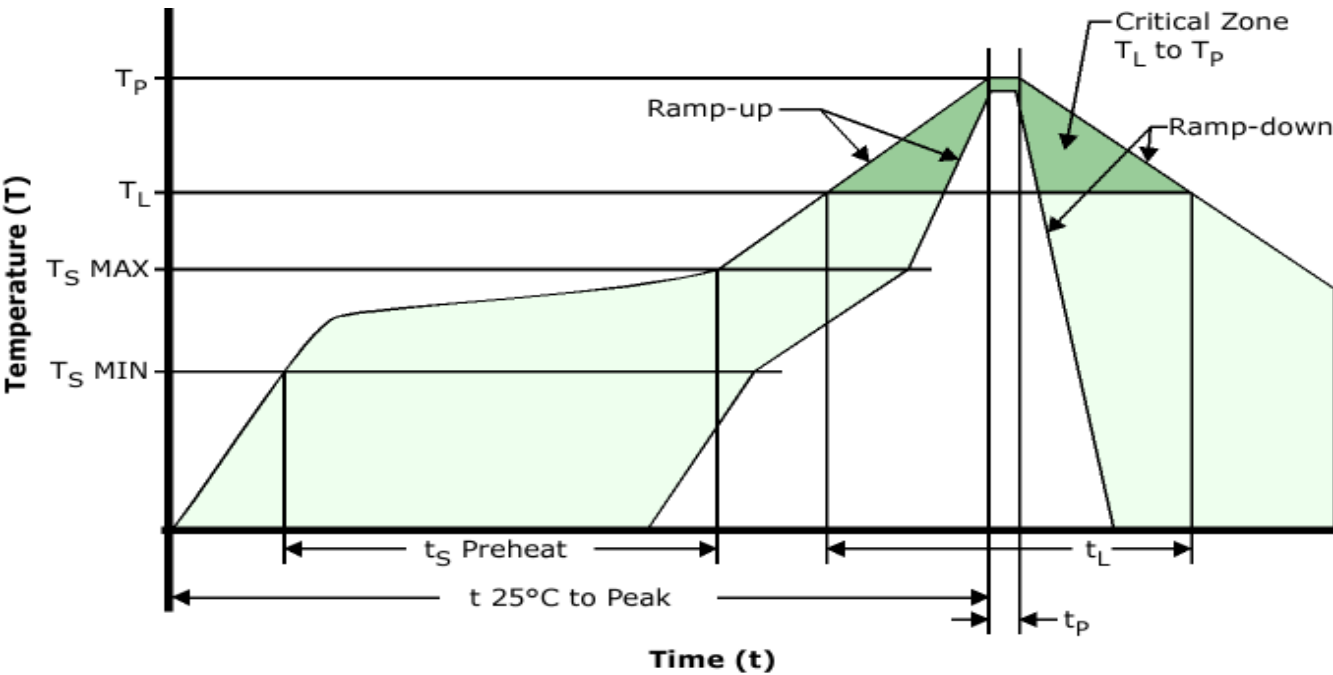
Note 1: An external 0.01μF ceramic bypass capacitor in parallel with a 0.1μF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

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Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

Ts MAX to Tl (Ramp-up Rate)	5°C/Second Maximum
Preheat	
- Temperature Minimum (Ts MIN)	N/A
- Temperature Typical (Ts TYP)	150°C
- Temperature Maximum (Ts MAX)	N/A
- Time (ts MIN)	60 - 120 Seconds
Ramp-up Rate (Tl to Tp)	5°C/Second Maximum
Time Maintained Above:	
- Temperature (Tl)	150°C
- Time (tL)	200 Seconds Maximum
Peak Temperature (Tp)	240°C Maximum
Target Peak Temperature (Tp Target)	240°C Maximum 2 Times / 230°C Maximum 1 Time
Time within 5°C of actual peak (tp)	10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time
Ramp-down Rate	5°C/Second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum.